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(54) **ELECTRO-OPTICAL DEVICE, SUBSTRATE FOR ELECTRO-OPTICAL DEVICE, AND PROJECTING TYPE DISPLAY DEVICE**

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(57) **ABSTRACT**

An electro-optical device includes, on a TFT array substrate, pixel electrodes, TFTs connected to the pixel electrodes, a shading layer that covers at least the channel regions of the TFTs, and a light absorption layer interposed between the shading layer and the TFTs and mainly formed a material which mainly forms the channel regions. The light absorption layer suppresses occurrence of inner surface reflection and multiple reflection on the inner surface of the shading layer facing the TFTs.

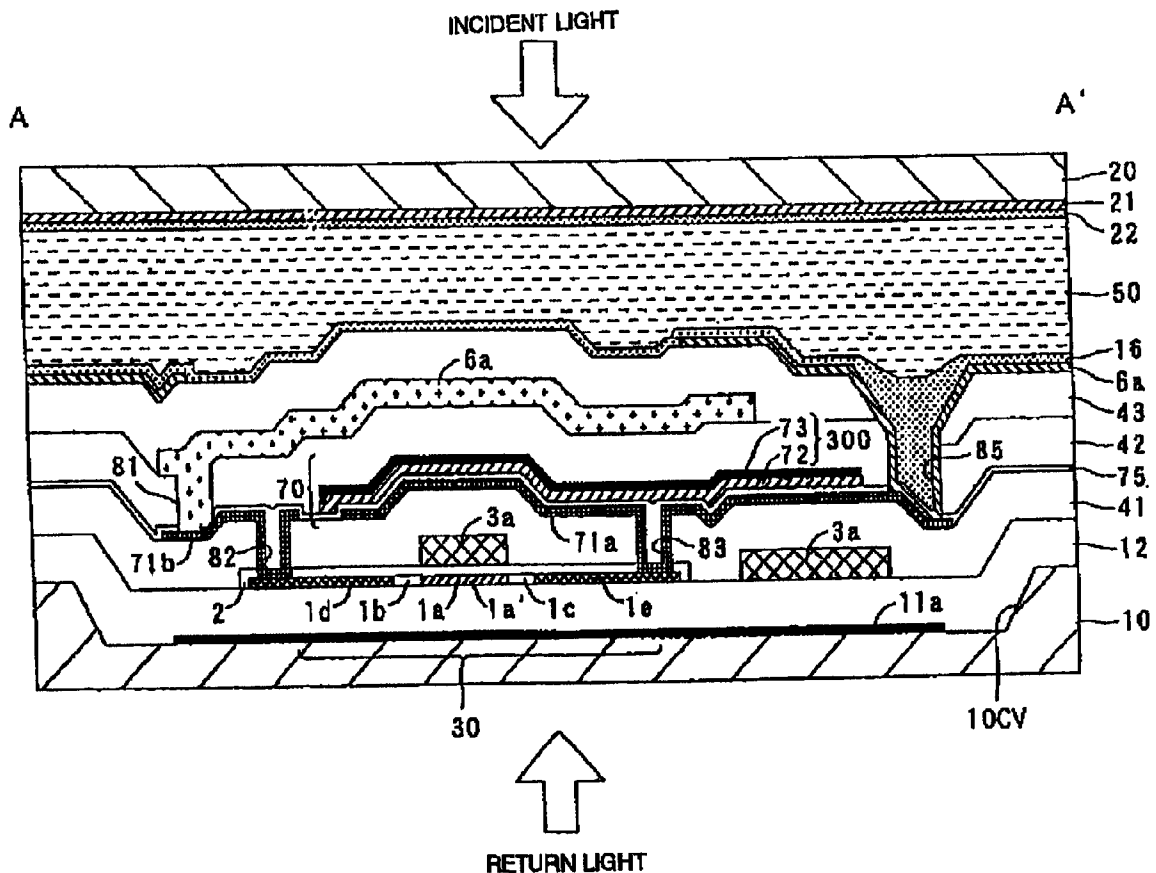


Fig. 1

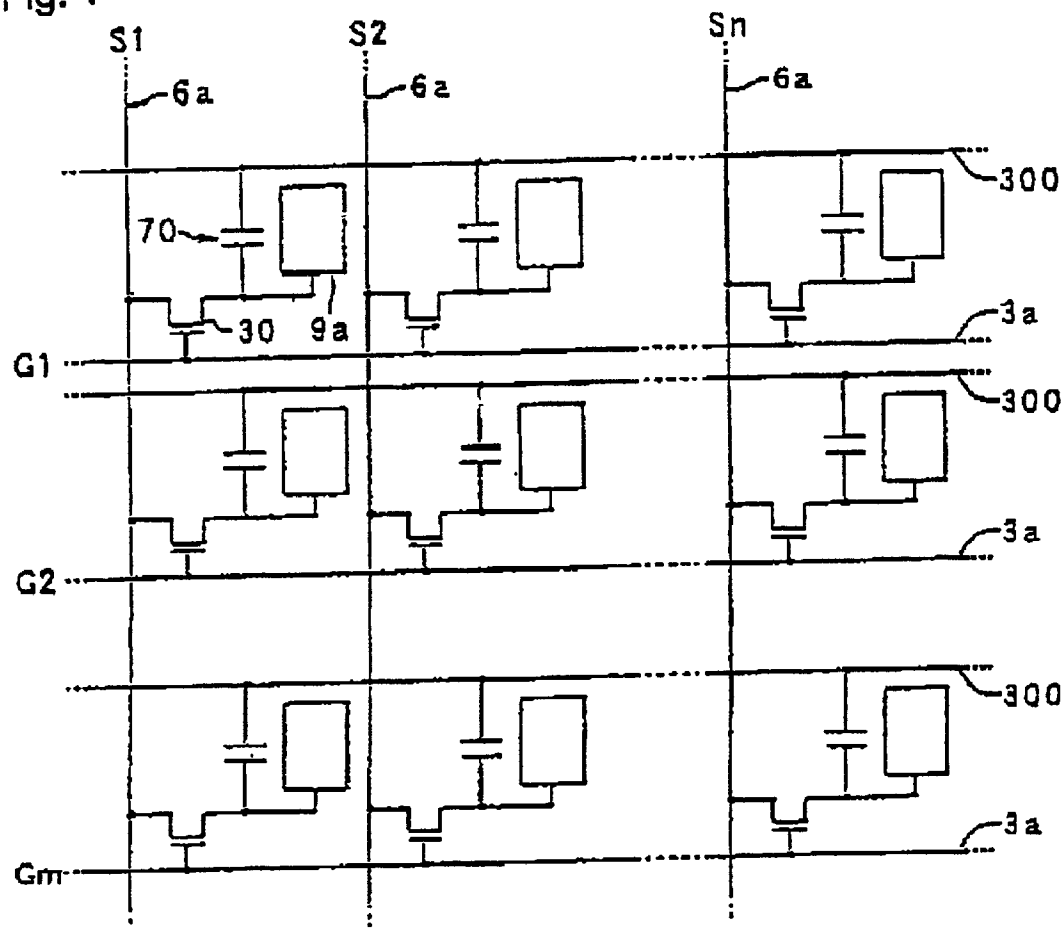


Fig. 2

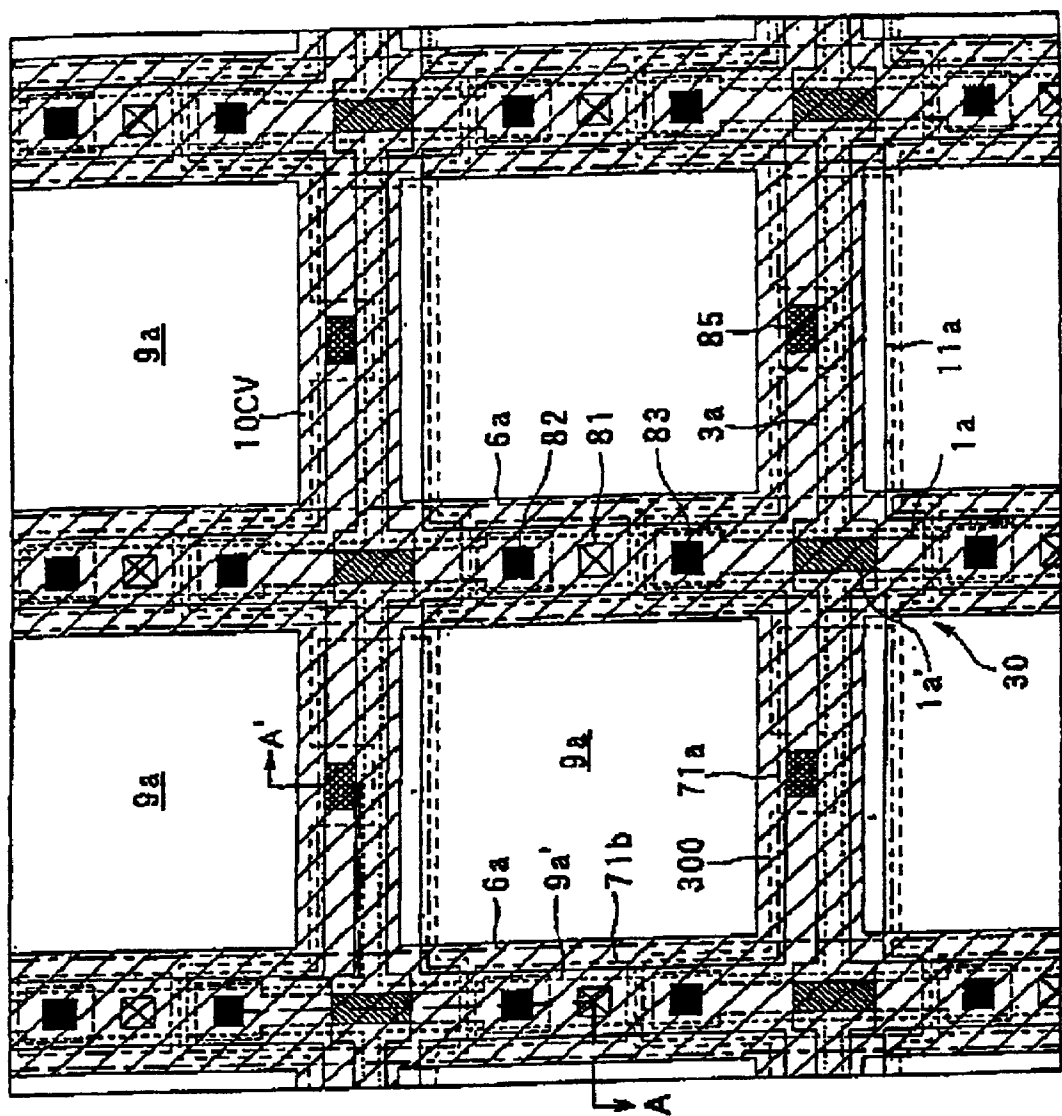


Fig. 4

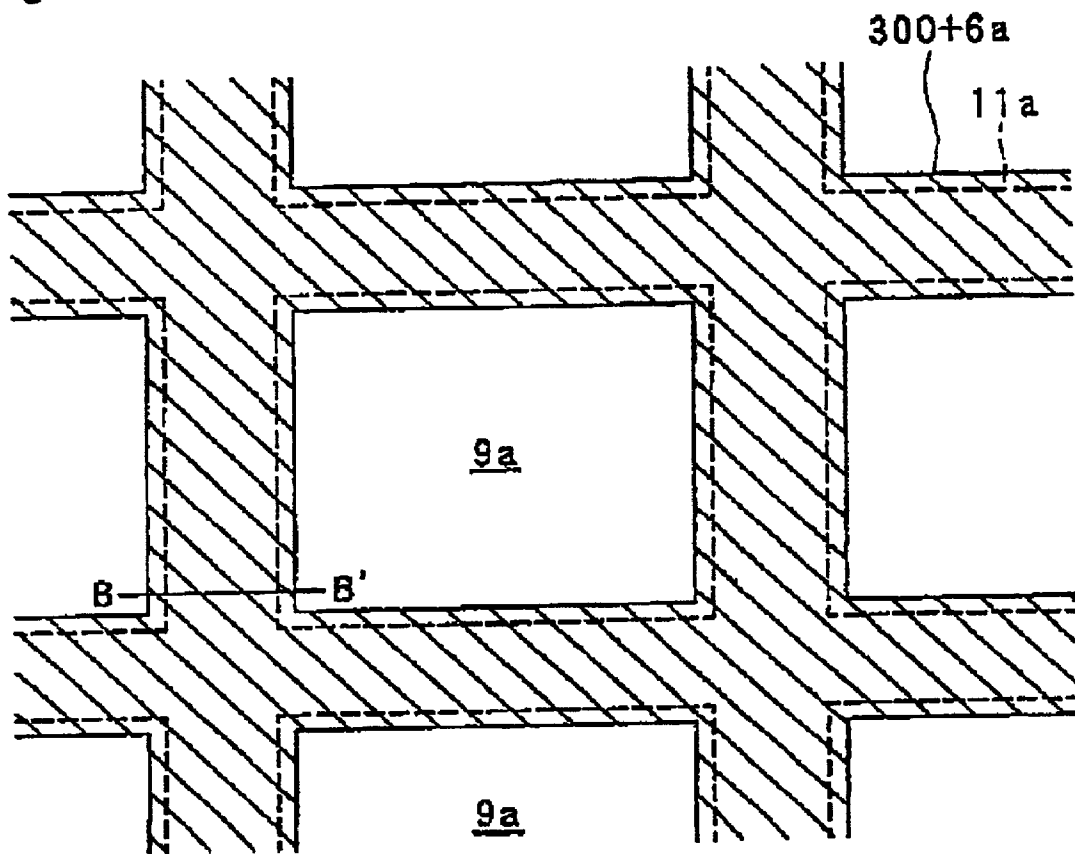


Fig. 5

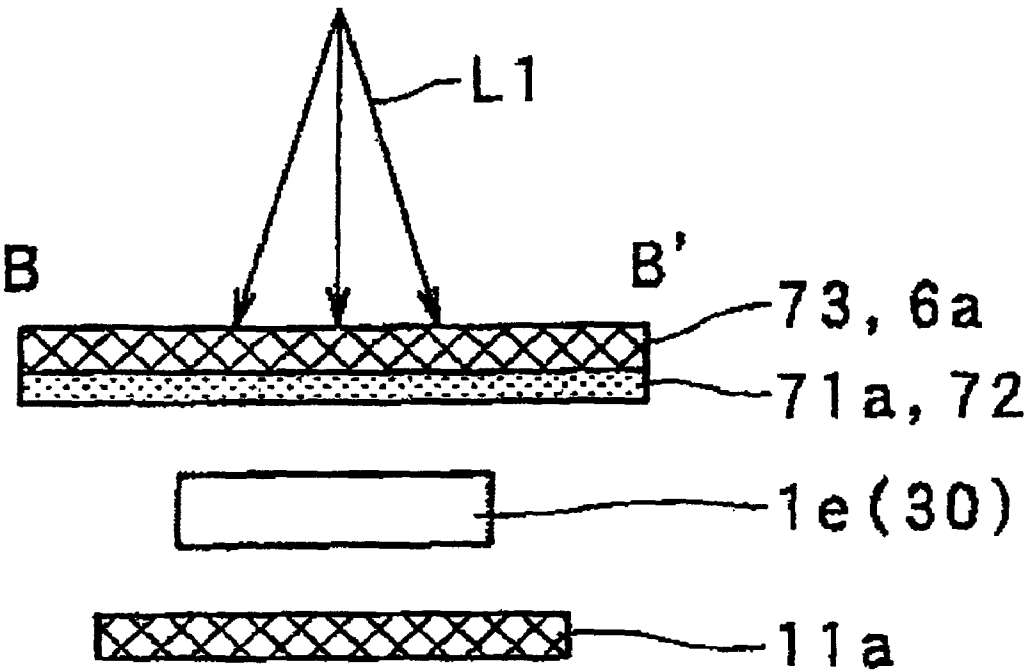


Fig. 6

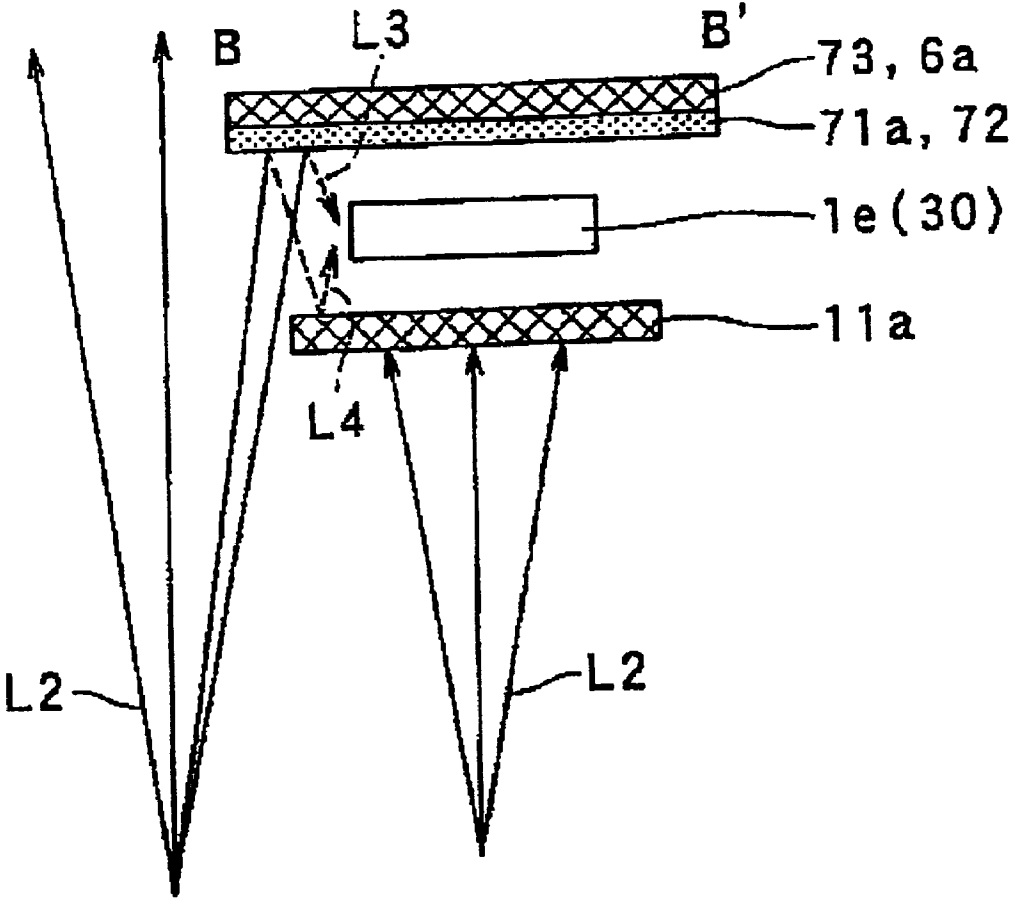


Fig. 7

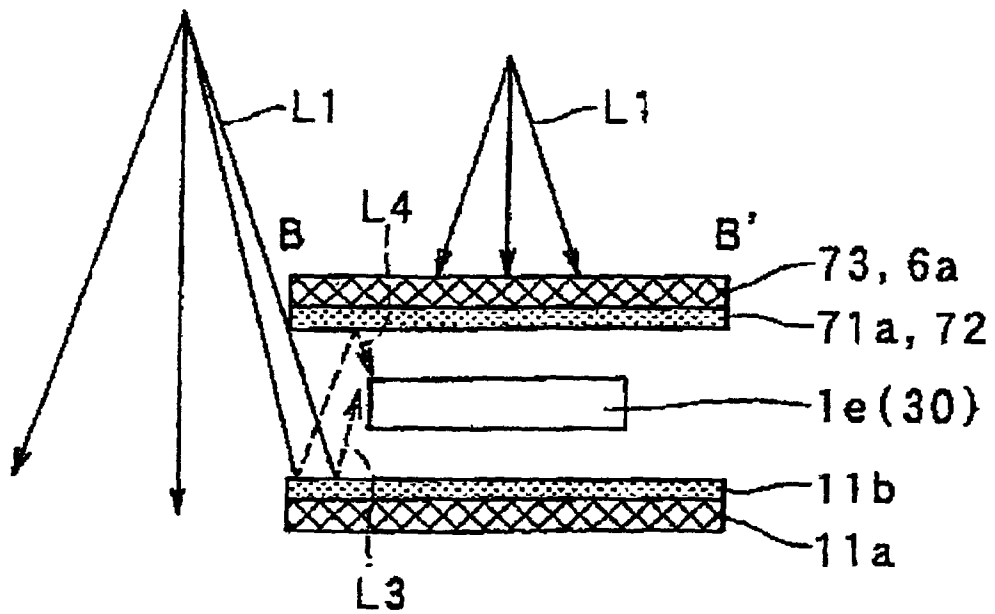


Fig. 8

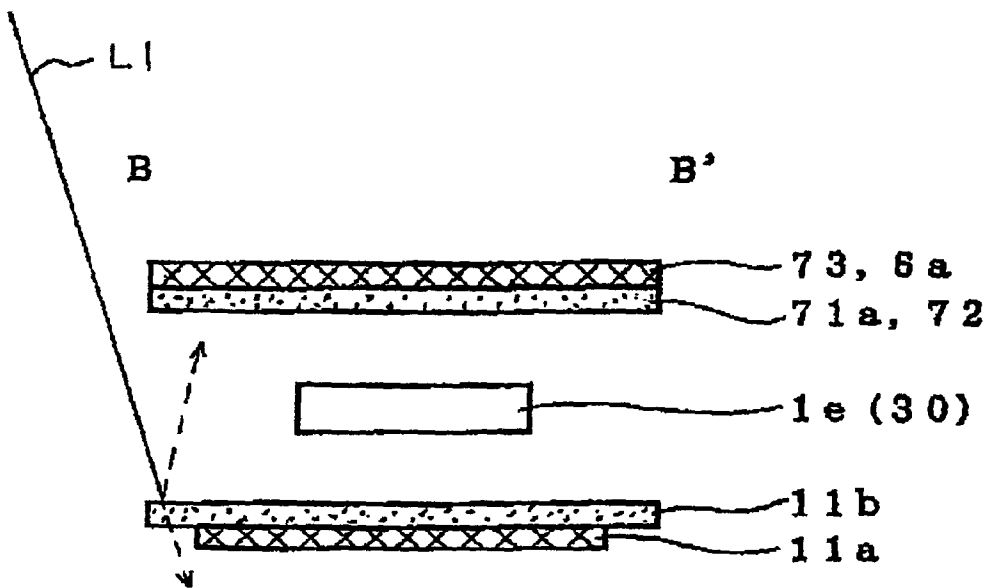


Fig. 9

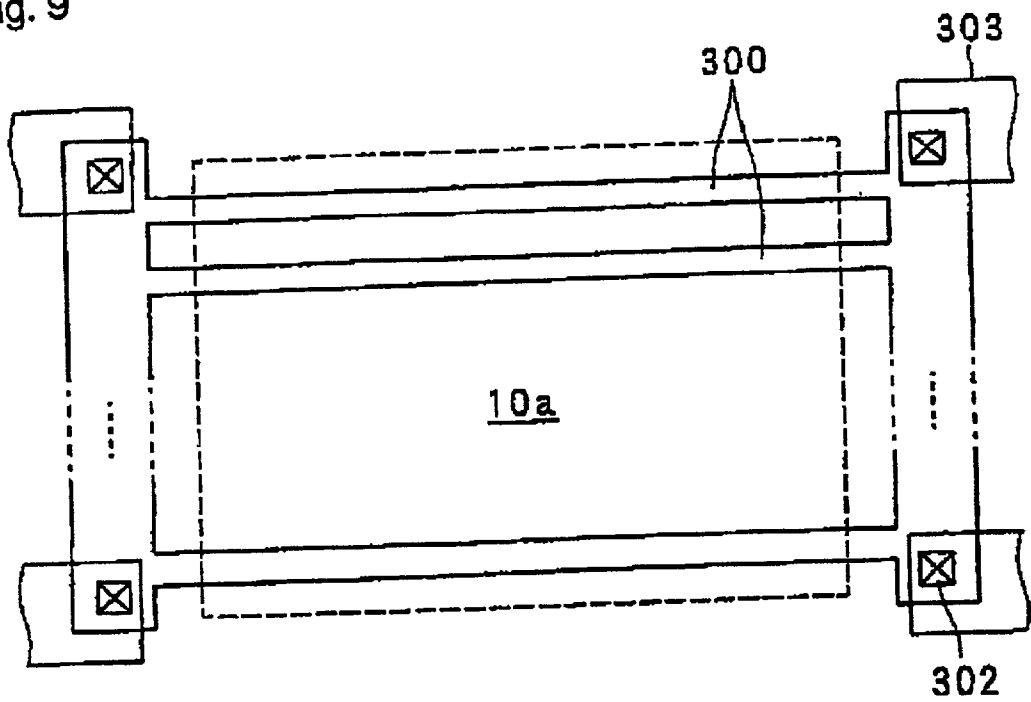


Fig. 10

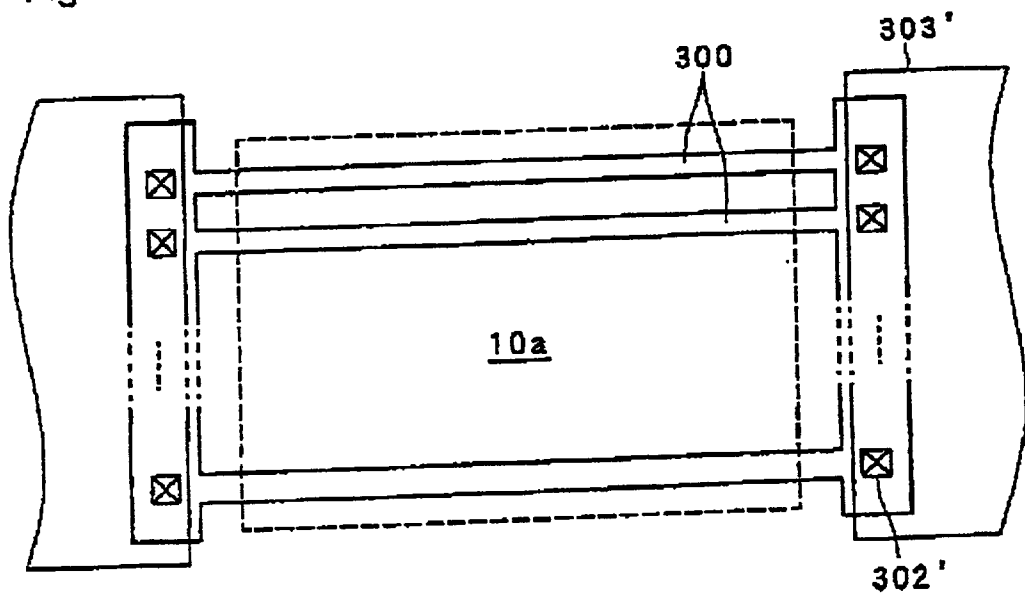


Fig. 11

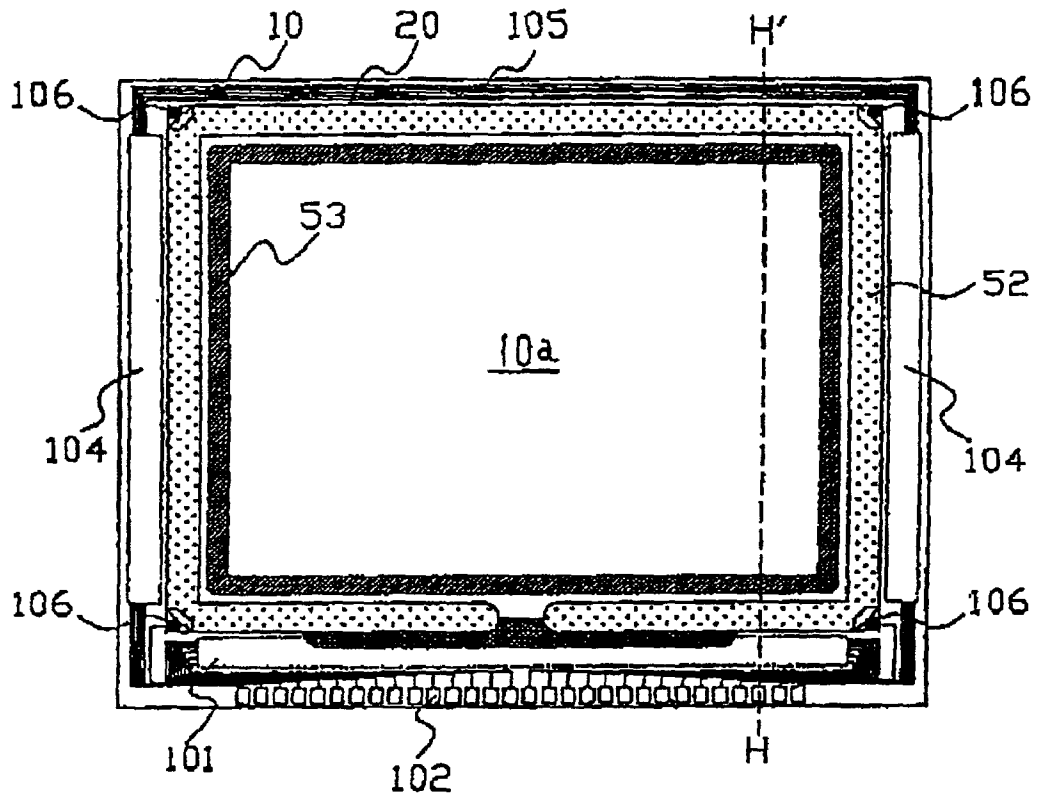


Fig. 12

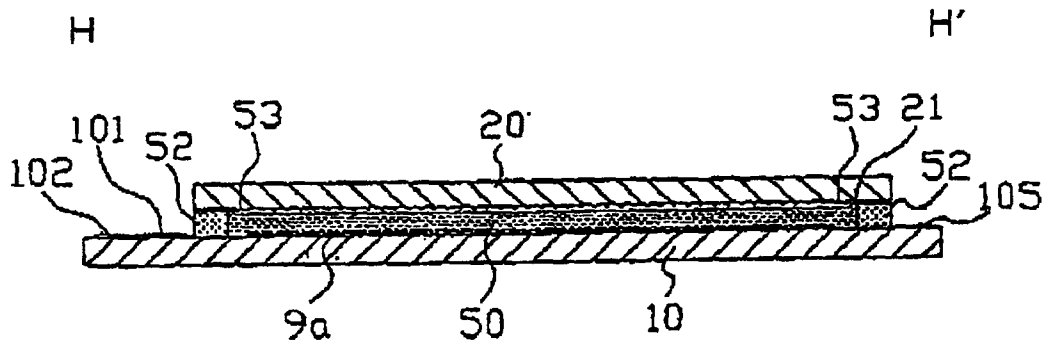
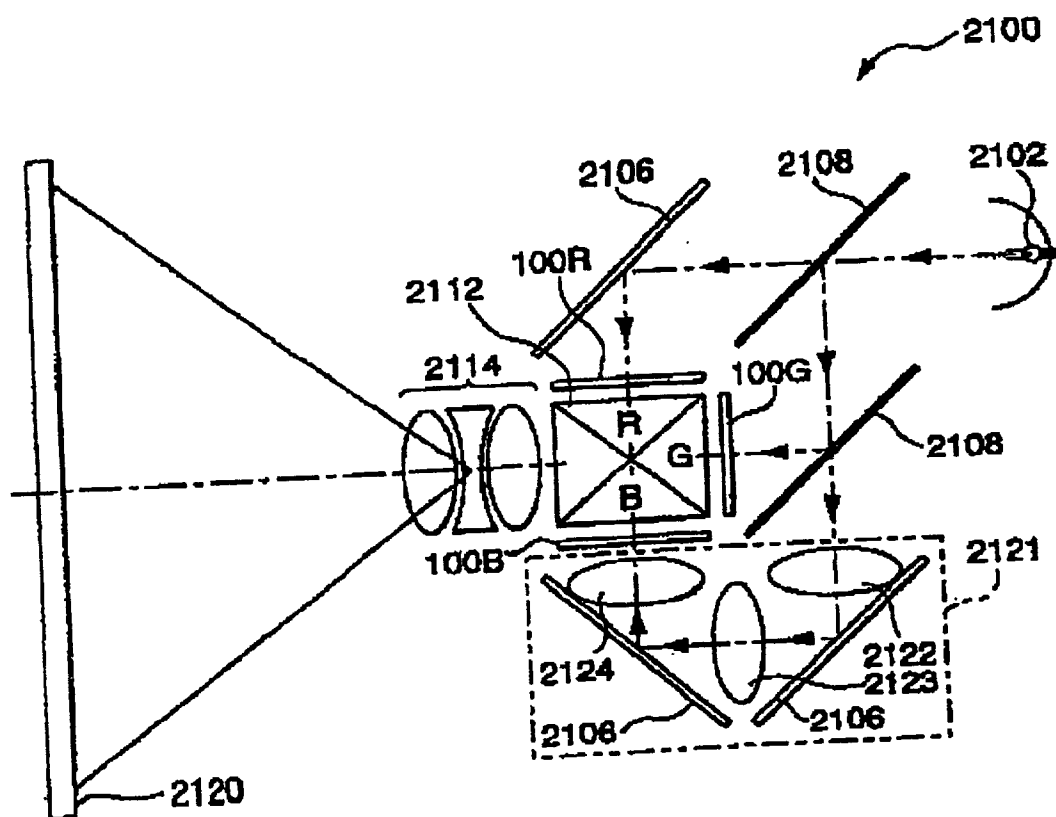


Fig. 13



ELECTRO-OPTICAL DEVICE, SUBSTRATE FOR ELECTRO-OPTICAL DEVICE, AND PROJECTING TYPE DISPLAY DEVICE

BACKGROUND OF THE INVENTION

[0001] 1. Field of Invention

[0002] The present invention relates to the technical field of an electro-optical device of an active matrix drive system, and more particularly, to the technical field of an electro-optical device of a type having pixel switching thin film transistors (hereinafter, referred to as TFTs) disposed in a laminated layer structure on a substrate.

[0003] 2. Description of Related Art

[0004] In electro-optical devices of a TFT active matrix drive system, when incident light beams are irradiated on the channel region of a pixel switching TFT associated with each pixel, a current is generated thereto by the excitation caused by the light beams so that the characteristics of the TFT are changed. In particular, in electro-optical devices used for light bulbs of projectors, since incident light beams have high intensity, it is important to shade light beams incident on the channel region and its peripheral region of a TFT. Thus, the channel region and its peripheral region are conventionally shaded by a shading film disposed at a confronting substrate to prescribe the opening region of each pixel or by a data line passing on the TFT and formed of a metal film of Al or the like. Japanese Unexamined Patent Application Publication No. 9-33944 discloses a technology for reducing light beams incident on a channel region by a shading film formed of a-Si (amorphous silicon) having a large refractive index. Further, a shading film formed of, for example, a metal having a high melting point, is sometimes disposed on a TFT array substrate at a position facing a pixel switching TFT (that is, below the TFT). The shading film also disposed below the TFT can prevent light beams reflected on the back surface of the TFT array substrate from being incident on the TFT of the electro-optical device as well as can prevent projected light beams, which have passed through a prism and the like when one optical system is constructed by a combination of a plurality of electro-optical devices through the prism and the like, from being incident on the TFT of the electro-optical device.

SUMMARY OF THE INVENTION

[0005] However, the above-mentioned various types of the shading technologies have the following problems. That is, first, according to the technology for forming the shading film on the confronting substrate and on the TFT array substrate, the shading film is considerably separated from the channel region through, for example, a liquid crystal layer, electrodes, an interlayer insulation film when observed three-dimensionally, and light beams incident obliquely between the shading film and the channel region cannot be sufficiently shaded. In particular, in small electro-optical devices used as light bulbs of projectors, light beams incident thereon are obtained by stopping light beams projected from a light source through a lens and that contain an obliquely incident light component in an amount which cannot be disregarded. Thus, it is a problem in practical use that such obliquely incident light beams are not sufficiently shaded.

[0006] In addition to the above problems, after light beams, which have traveled into an electro-optical device from a region having no shading film, and are reflected by a shading film and the inner surface of a data line (that is, the surface thereof facing a channel region), the reflected light beams, or light beams, which are created when the reflected light beams are further reflected by the shading film and the inner surface of the data line a plurality of times (hereinafter, referred to as "multipath-reflected light beams"), may finally reach the channel region of a TFT. Further, according to the technology for shading light beams by a data line, it is basically difficult for the data line to sufficiently shade light beams, because the data line is formed in a striped shape which extends perpendicularly to a scanning line when observed on a plan view. It is also necessary to dispose a thick interlayer insulation film therebetween in such a degree that the adverse affect of the capacitance coupling between the data line and the channel region can be disregarded.

[0007] Further, according to the technology described in Japanese Unexamined Patent Application Publication No. 9-33944, a relatively thick interlayer insulation film must be laminated between a gate electrode and an a-Si film to reduce the adverse affect of the capacitance coupling therebetween to form an a-Si film on a gate line. As a result, the additional formation of the a-Si film, the interlayer insulation film, and the like makes a laminated structure complex and increases its size. It is also difficult to sufficiently shade obliquely incident light beams and inner-surface reflected light beams. In particular, since electro-optical devices are miniaturized and the pixel pitches thereof are greatly narrowed to cope with a recent requirement for enhancing the quality of a displayed image, it is more difficult to sufficiently shade light beams by the various types of the above-mentioned conventional technologies. Accordingly, a problem arises in that the quality of a displayed image is lowered by flickering of the image and the like caused by the change of the characteristics of TFTs.

[0008] It should be noted that, while it is contemplated to increase a region where a shading film is formed to increase the light resistant property, an increase in the region where the shading film is formed causes a problem in that it is fundamentally difficult to increase the opening ratio of each pixel in order to enhance the brightness of a displayed image.

[0009] It is therefore an object of the present invention, which was made in view of the above-mentioned problems, to provide an electro-optical device which is excellent in its light resistant property, and which has a relatively large opening ratio of each pixel and can display an image of high quality.

[0010] To solve the above problems, an electro-optical device of the present invention includes a pair of substrates, an electro-optical substance interposed between the pair of substrates, pixel electrodes formed on one of the pair of substrates, thin film transistors connected to the pixel electrodes, a shading layer that covers at least the channel regions of the thin film transistors, and a light absorption layer interposed between the shading layer and the thin film transistors.

[0011] According to the electro-optical device of the present invention, at least the channel regions of the thin film transistors connected to the pixel electrodes are shaded by the shading layer.

[0012] When a shading layer formed of a metal film having a shading property such as an Al (aluminum) film, a Cr (chromium) film, or the like is generally used, light beams incident on the thin film transistors from a side where the shading layer is disposed basically can be sufficiently shaded by reflecting the light beams by the surface, which does not face the thin film transistors, of the shading layer (that is, by the outer surface of the shading layer in the electro-optical device). More specifically, when the shading layer is disposed on a side where light beams (for example, projected light beams when the electro-optical device is applied to a projector) are incident on the thin film transistors, the incident light beams can be shaded by the outer surface of the shading layer. Otherwise, when the shading layer is disposed on a side from which incident light beams emerge with respect to the thin film transistors, return light beams (for example, light beams reflected on a back surface when the electro-optical device is applied to the projector, light beams passing through a composite optical system from other light bulb when a plurality of electro-optical devices are used in combination as a light bulb as in a case in which the electro-optical devices are applied to a double-panel type projector) can be shaded by the outer surface of the shading layer. However, return light beams, which pass aside the thin film transistors from an opposite side of the shading layer and are oblique to the substrate (for example, when the shading layer is disposed to the side of the thin film transistors on which light beams are incident) or incident light beams (for example, when the shading layer is disposed to the side of the thin film transistors from which light beams emerge) are at least partly reflected by the front surface, which faces the thin film transistors, of the shading layer (that is, the inner surface of the shading layer in the electro-optical device). Thus, inner-surface-reflected light beams are generated between the shading layer and the thin film transistors by these oblique incident light beams and return light beams reflected on the inner surface of the shading layer. Further, multiple reflection is also caused when the inner-surface-reflected light beams are reflected by another film. Accordingly, even if the shading layer is simply disposed at the thin film transistors, inner-surface-reflected light beams and multipath-reflected light beams are caused by light beams reflected by the inner surface of the shading layer and finally incident on the thin film transistors, regardless of the size of the shading layer and the location where the shading layer is disposed. As a result, the characteristics of the thin film transistors are deteriorated by these internally-reflected light beams and multipath-reflected light beams.

[0013] According to the present invention, however, light beams, which pass aside the thin film transistors from the opposite side of the shading layer and tend to obliquely reach the inner surface of the shading layer, and light beams, which are reflected by the inner surface of the shading layer, are absorbed by the light absorption layer interposed between the shading layer and the thin film transistors. As a result, when the shading layer formed of the metal film having a high reflectance, such as the Al film, the Cr film is disposed and sufficiently shades light beams incident on the outer surface of the shading layer, the transistor character-

istics can be effectively prevented from being deteriorated by light leakage. Further, reduction of a contrast ratio caused by light beams passing through an image display region can be effectively prevented by the shading layer. On the other hand, since the inner-surface-reflected light beams and the multipath-reflected light beams are absorbed by the light absorption layer, the deterioration of the transistor characteristics caused by the light leakage can be more effectively reduced or prevented. Moreover, light beams can be shaded and absorbed at a location relatively near to the thin film transistors as compared with a case in which they are shaded and absorbed by, for example, a shading layer disposed to a conventional confronting substrate, which can enhance a shading performance while avoiding an unnecessarily increase in a region where the shading layer is formed (that is, without unnecessarily reducing the non-opening region of each pixel).

[0014] As a result, an electro-optical device can be realized in which respective pixels have a high opening ratio. Also, deterioration of the characteristics of thin film transistors due to light leakage can be reduced by a high light resistant property. An electron optical device can be provided, which has a high contrast ratio, and which can display an image of high quality.

[0015] It should be noted that the interlayer distance between the shading layer and the light absorption layer in the present invention may be small by interposing no film or a very thin insulation film, or the like therebetween, or may be large by interposing a somewhat thick interlayer insulation film therebetween. As described below, however, it is advantageous to reduce the interlayer distance between the shading layer and the light absorption layer from a view point of constructing a storage capacitor by using the shading layer and the light absorption layer as a pair of capacitance electrodes, and from a view point of enabling heat generated by the light absorption layer to escape, through the shading layer.

[0016] In one aspect of the electro-optical device of the present invention, the light absorption layer is mainly formed of a material which mainly forms the channel regions of the thin film transistors. The light absorption layer is formed of a polysilicon film mainly formed of, for example, silicon and containing P, B, or As doped thereto to make the silicon conductive.

[0017] Further, the channels of the thin film transistors are formed of polysilicon mainly including silicon. The polysilicon is doped with a slight amount of B, P, As or the like to control the threshold voltage V_{th} of the thin film transistors, or is not doped with any material.

[0018] Further, amorphous silicon or single crystal silicon may be used for the channels and the light absorption layer in place of the polysilicon.

[0019] In another aspect of the electro-optical device of the present invention, the light absorption layer is formed of a silicon film.

[0020] According to this aspect, light beams, which tend to reach the inner surface of the shading layer, and light beams, which are reflected by the inner surface, can be absorbed by the light absorption layer formed of the silicon film. Therefore, the occurrence of the inner-surface-reflected light beams and the multipath-reflected light beams can be

effectively reduced or prevented. In particular, when the polysilicon film is employed as a semiconductor layer serving as the channel regions of the thin film transistors, the light absorption layer has a light absorbing property that is similar to, or the same as, the light absorbing property (frequency depending property and the like) in the channel regions. Accordingly, the light absorption layer formed of the silicon film is very advantageous because light beams including a light component, which becomes a cause of light leakage when absorbed by the channel regions, can be absorbed and removed by the light absorption layer.

[0021] In another aspect of the electro-optical device of the present invention, the shading layer is formed of a film containing metal.

[0022] According to this aspect, incident light beams and return light beams can be sufficiently shaded by the shading layer formed of the film containing metal. At this time, since internally-reflected light beams and multipath-reflected light beams can be particularly absorbed and removed by the light absorption layer, a film containing metal having a very high reflectance, such as an A1 film, and the like, can be employed. It should be noted that exemplified as the film containing metal, in addition to the A1 film, is a film formed of single metal, alloy, metal silicide, polysilicide, a laminated film thereof, and the like, containing at least one of high melting point metals, for example, Ti (titanium), Cr (chromium), W (tungsten), Ta (tantalum), Mo (molybdenum), Pb (lead), and the like.

[0023] In another aspect of the electro-optical device of the present invention, the shading layer is disposed above the thin film transistors on the substrate.

[0024] According to this aspect, incident light beams can be shaded by the outer surface of the shading layer disposed above the thin film transistors. Then, since return light beams, which tend to reach the inner surface of the shading layer, and light beams, which are reflected by the inner surface thereof, are absorbed and removed by the light absorption layer, the deterioration of the characteristics of the thin film transistors due to the internally-reflected light beams and the multipath-reflected light beams resulting from the reflection of light beams on the inner surface of the shading layer can be reduced or prevented by the shading layer and the light absorption layer.

[0025] In the aspect in which the shading layer is disposed on the upper side, the shading layer may be formed of data lines.

[0026] With this arrangement, when data lines composed of an A1 film, or the like, are provided with a function as a shading layer in addition to a function as wiring, it is possible to prevent a laminated structure from becoming complex by additionally forming a dedicated shading layer. Accordingly, this arrangement is very advantageous by simply arranging the electro-optical device, and simplifies a manufacturing process thereof.

[0027] In the aspect in which the shading layer is disposed on the upper side, the shading layer may be formed of capacitance lines interposed between the data lines and the thin film transistors, and the light absorption layer may be formed of capacitance electrodes disposed in confrontation with the capacitance lines through a dielectric film and separated in an island shape for each pixel.

[0028] With this arrangement, the provision of the function as the shading layer with the capacitance lines formed of the metal film, the polysilicon film, or the like, in addition to the function as the wiring, as well as the provision of the function as the light absorption layer with the capacitance electrodes formed of the polysilicon film, or the like, in addition to the function as the electrodes, prevents the laminated structure from becoming complex by additionally forming a dedicated shading layer and a dedicated light absorption layer. Accordingly, this arrangement is very advantageous by simply arranging the electro-optical device, and simplifies a manufacturing process thereof.

[0029] In the aspect in which the shading layer is disposed on the upper side, the shading film may be formed of a plurality of data lines connected to the thin film transistors and extending in a first direction, respectively, and a plurality of capacitance lines connected to the pixel electrodes and extending in a second direction intersecting the first direction, respectively.

[0030] With this arrangement, the provision of the function as a part of the shading layer with the data lines formed of the A1 film, or the like, in addition to the function as the wiring, as well as the provision of the function as a part the shading layer with the capacitance lines formed of the metal film, polysilicon film, or the like, in addition to the function as the wiring, prevents the laminated structure from becoming complex by additionally forming a dedicated shading layer. In particular, when the data lines are used as the shading layer in the direction along the data lines, and the capacitance lines are used as the shading layer in the direction along the capacitance lines or scanning lines, no waste is caused in the layout of wiring. Accordingly, this arrangement is very advantageous by simply arranging the electro-optical device, and simplifies a manufacturing process thereof.

[0031] Otherwise, according to this aspect in which the shading layer is disposed on the upper side, the shading layer may be formed of one layer of capacitance lines interposed between data lines and the thin film transistors, and having a multilayer structure, and the light absorption layer may be formed of another layer of the capacitance lines that is located nearer to the thin film transistors than the one layer.

[0032] With this arrangement, both a shading function and a light absorbing function can be provided by the capacitance lines, which have the multi-layer structure, including both the shading layer and the light absorption layer. In addition to the above, it is also possible to enable heat generated in the light absorption layer when it absorbs light beams to escape through the shading layer.

[0033] Further, in various situations in which the capacitance lines are provided as described above, the capacitance lines may be formed in a striped shape extending in a direction intersecting the data lines in an image display region, and may be connected to a constant potential source located in a peripheral region located in the vicinity of the image display region.

[0034] With this arrangement, the capacitance lines can be set to a constant potential in the peripheral region, so that the constant potential portion of the capacitance lines, that is disposed facing the respective capacitance electrodes in the image display region, can suitably function as fixed potential

side capacitance electrodes constituting a storage capacitor. Therefore, the performance of the storage capacitor can be enhanced. The constant potential source may be a constant potential source, such as a positive power supply or a negative power supply, which is supplied to a periphery drive circuit to drive the thin film transistors, or a constant potential source supplied to the confronting electrodes of the confronting substrate.

[0035] When the capacitance lines are connected to the constant potential source as described above, the capacitance lines may be connected to each other in the peripheral region, and may be connected to the constant potential source as a whole through one or a plurality of contacts.

[0036] With this arrangement, in the image display region, the plurality of striped-shaped capacitance lines can be connected to the constant potential as a whole in the peripheral region through the one or plurality of contacts (for example, the contacts disposed at the four corners of the substrate).

[0037] Otherwise, when the capacitance lines are connected to the constant potential source as described above, the capacitance lines may be connected to each other in the peripheral region, and may be redundantly connected to the constant potential source as a whole through a plurality of contacts.

[0038] With this arrangement, in the image display region, the plurality of striped-shaped capacitance lines can be stably and reliably connected to the constant potential in the peripheral region through the plurality of contacts disposed redundantly.

[0039] Further, according to this aspect in which the shading layer is disposed on the upper side as described above, another shading layer may further be provided, which is disposed below the thin film transistors on the substrate, to cover at least the channel regions of the thin film transistors.

[0040] With this arrangement, return light beams, traveling from the lower side of the thin film transistors, can be shaded by the other shading film so that the thin film transistors can be shaded from the upper and lower sides thereof. At this time, internally-reflected light beams and multipath-reflected light beams, which particularly tend to be created between the two shading films, can be absorbed and shaded by the light absorption layer. The other shading film may be formed of single metal, alloy, metal silicide, poly-silicide, a laminated film thereof, or the like, containing at least one of high melting point metals, for example, Ti, Cr, W, Ta, Mo, Pb.

[0041] In this case, the other light absorption layer may be interposed between the other shading layer and the thin film transistors. The other light absorption layer being mainly formed of a material (for example, silicon or polysilicon) which mainly forms the channel regions of the thin film transistors.

[0042] With this arrangement, the internally-reflected light beams and the multipath-reflected light beams, which tend to be created between the two shading films, can more strongly be absorbed and shaded by the two light absorption layers.

[0043] In another aspect of the electro-optical device of the present invention, the shading layer is disposed below the thin film transistors on the substrate.

[0044] According to this aspect, return light beams can be shaded by the outer surface of the shading layer disposed below the thin film transistors. Then, since incident light beams, which tend to reach the inner surface of the shading layer, and light beams, which are reflected by the inner surface thereof, are absorbed and removed by the light absorption layer, the deterioration of the characteristics of the thin film transistors due to the internally-reflected light beams and the multipath-reflected light beams resulting from the reflection of light beams on the inner surface of the shading layer can be reduced or prevented by the shading layer and the light absorption layer. The shading film disposed below the thin film transistors may be formed of single metal, alloy, metal silicide, poly-silicide, a laminated film thereof, or the like, containing at least one of high melting point metals, for example, Ti, Cr, W, Ta, Mo, Pb.

[0045] In another aspect of the electro-optical device of the present invention, the light absorption layer includes a portion that includes an intermediate conductor layer that transits and connects the pixel electrodes or the data lines to the thin film transistors.

[0046] According to this aspect, the provision of the function as a part of the light absorption layer with the intermediate conductor layer formed of the polysilicon film, or the like, in addition to the transiting and connecting function, can prevent the laminated structure from becoming complex by additionally forming a dedicated light absorption layer. Accordingly, this arrangement is advantageous by simply arranging the electro-optical device, and simplifies a manufacturing process thereof. It should be noted that when the intermediation and connection are executed by making use of the intermediate conductor layer, the connection between the thin film transistors and the pixel electrodes, and between the thin film transistors and the data lines, can be excellently performed through at least two series contact holes, each having a relatively small diameter, while avoiding a technical difficulty of executing the connection through one contact hole, even if the distance between the thin film transistors and the pixel electrodes, and the distance between the thin film transistors and the data lines, is long.

[0047] In another aspect of the electro-optical device of the present invention, the shading layer has a heat conductivity that is higher than that of the light absorption layer.

[0048] According to this aspect, it is possible for heat generated in the light absorption layer when it absorbs light beams through the shading layer having the high heat conductivity to escape. That is, the quantity of heat transmitted from the light absorption layer to the thin film transistors can be reduced, whereby heat leakage generated in the thin film transistors can be reduced. As a result, the transistor characteristics can be greatly enhanced by reducing both the light leakage and the heat leakage by the shading film and the light absorption layer.

[0049] In this aspect, the interlayer distance between the thin film transistors and the light absorption layer may be larger than that between the light absorption layer and the shading layer.

[0050] With this arrangement, it is possible to more effectively escape heat generated in the light absorption layer,

when it absorbs light beams through the shading layer disposed in the vicinity of the light absorption layer. That is, the quantity of heat transmitted to the thin film transistors can be reduced by the distance of the light absorption layer disposed farther. An interlayer insulation film or the like is interposed between the thin film transistors and the light absorption layer, and between the light absorption layer and the shading layer.

[0051] In another aspect of the electro-optical device of the present invention, the shading layer is laminated on the light absorption layer through an insulation film, and is formed slightly larger than the light absorption layer when observed in plan view.

[0052] According to this aspect, light beams incident on the outer surface of the shading layer, which is slightly larger than the light absorption layer, can be shaded by the shading film, and, at the same time, light beams, incident on the inner surface of the shading layer, can be absorbed by the light absorption layer, which is slightly smaller than the shading layer.

[0053] In another aspect of the present invention, an electro-optical device includes a pair of substrates, an electro-optical substance interposed between the pair of substrates, a pixel electrodes formed on one of the pair of substrates thin film transistors connected to the pixel electrodes, a first shading layer that covers at least the channel regions of the thin film transistors, and a first light absorption layer facing the first shading layer through the thin film transistors.

[0054] According to this aspect, the light beams incident on the thin film transistors are shaded by the first shading layer and absorbed by the first light absorption layer, so that the light beams are prevented from being reflected to the thin film transistors.

[0055] Further, it is preferable that the first shading layer be disposed on a light incident side with respect to the thin film transistors.

[0056] According to this aspect, the first shading layer can prevent light beams from being directly irradiated to the thin film transistors.

[0057] Further, it is preferable that a second light absorption layer be interposed between the first shading layer and the thin film transistors.

[0058] According to this aspect, the light beams directed to the thin film transistor side of the first shading layer by internal reflection and the like can be absorbed by the second light absorption layer.

[0059] Further, it is preferable that a second shading layer be disposed on a side opposite to the first light absorption layer with respect to the thin film transistors.

[0060] According to this aspect, the light beams directed to the thin film transistors by internal reflection and the like can be shaded by the second shading layer.

[0061] Further, the second shading layer may be formed in a region inside of the first light absorption layer.

[0062] According to this aspect, even if strong light beams are obliquely irradiated to the first light absorption layer

extending from the second shading layer and leak from the first light absorption layer, the light beams can escape to the exterior.

[0063] Further, the second shading layer is formed in a region inside of the first shading layer.

[0064] According to this aspect, the second shading layer can avoid oblique light beams.

[0065] In another aspect of the electro-optical device of the present invention, the electro-optical device includes a pair of substrates, an electro-optical substance interposed between the pair of substrates, pixel electrodes formed on one of the pair of substrates, thin film transistors connected to the pixel electrodes, a first light absorption layer that covers at least the channel regions of the thin film transistors, and a second light absorption layer facing the first light absorption layer through the thin film transistors.

[0066] According to this aspect, obliquely incident light beams in particular can be absorbed by the first and second light absorption layers, which can reduce light beams irradiated to the thin film transistors.

[0067] Further, light transmitting insulation films are interposed among the pixel electrodes, the thin film transistors, and the first light absorption layer, respectively.

[0068] In an aspect of a projecting type display device of the present invention, the projecting type display device includes a light source, light bulbs, each including an electro-optical device, light conductors that introduce light beams emitted from the light source to the light bulbs, and a projecting optical member that projects light beams modulated by the light bulbs.

[0069] According to this aspect, since it is difficult for light beams to enter the thin film transistors in the electro-optical device, an image of high quality can be projected.

[0070] In an aspect of a substrate for electro-optical device of the present invention, the substrate includes pixel electrodes, thin film transistors connected to the pixel electrodes, a shading layer that covers at least the channel regions of the thin film transistors, and a light absorption layer interposed between the shading layer and the thin film transistors.

[0071] In an aspect of the substrate for electro-optical device of the present invention, the substrate includes pixel electrodes, thin film transistors connected to the pixel electrodes, a first light absorption layer that covers at least the channel regions of the thin film transistors, and a second light absorption layer facing the first light absorption layer through the thin film transistors.

[0072] In an aspect of the substrate for electro-optical device of the present invention, the substrate includes pixel electrodes, thin film transistors connected to the pixel electrodes, a first light absorption layer that covers at least the channel regions of the thin film transistors, and a second light absorption layer facing the first light absorption layer through the thin film transistors.

[0073] The thin film transistors of the present invention may be of a so-called top gate type in which gate electrodes formed of a part of scanning lines are located above channel regions, or may be of a bottom type in which gate electrodes formed of a part of scanning lines are located below channel

regions. Further, the interlayer positions of pixel electrodes may be located above or below scanning lines on a substrate.

BRIEF DESCRIPTION OF THE DRAWINGS

[0074] FIG. 1 is a schematic of an equivalent circuit including various elements, wiring, and the like disposed at a plurality of matrix-shaped pixels constituting an image display region in an electro-optical device of an embodiment of the present invention;

[0075] FIG. 2 is a plan view of a plurality of adjacent pixel groups of a TFT array substrate, on which data lines, scanning lines, pixel electrodes, and the like are formed, in the electro-optical device of the embodiment;

[0076] FIG. 3 is a sectional view taken along plane A-A' of FIG. 2;

[0077] FIG. 4 is a plan view of a pixel of a TFT array substrate in the embodiment from which an upper layer shading film and a lower layer shading film are extracted and shown;

[0078] FIG. 5 is a pictorial sectional view showing how light beams are shaded and absorbed in the B-B' section of FIG. 4;

[0079] FIG. 6 is a pictorial sectional view showing how light beams are shaded and absorbed in the B-B' section of FIG. 4;

[0080] FIG. 7 is a pictorial sectional view showing how light beams are shaded and absorbed in the B-B' section of FIG. 4 in a modified embodiment;

[0081] FIG. 8 is a pictorial sectional view showing how light beams are shaded and absorbed in the B-B' section of FIG. 4 in another modified embodiment;

[0082] FIG. 9 is a plan view showing an example of an arrangement in which capacitance lines 300 are connected to a constant potential source;

[0083] FIG. 10 is a plan view showing another example of the arrangement in which the capacitance lines 300 are connected to the constant potential source;

[0084] FIG. 11 is a plan view of the TFT array substrate in the electro-optical device of the embodiment as viewed from a confronting substrate side together with the respective constitutional elements formed thereon;

[0085] FIG. 12 is a sectional view taken along plane H-H' of FIG. 11; and

[0086] FIG. 13 is a plan view showing an arrangement of a projector.

DETAILED DESCRIPTION OF PREFERRED EMBODIMENTS

[0087] Embodiments of the present invention will be described below based on the drawings. In the following embodiments, an electro-optical device of the present invention is applied to a liquid crystal device.

[0088] First, an arrangement of the electro-optical device in the embodiments of the present invention will be described with reference to FIGS. 1 to 3. FIG. 1 is a schematic of an equivalent circuit including various elements, wiring, and the like disposed at a plurality of matrix-

shaped pixels constituting the image display region of the electro-optical device. FIG. 2 is a plan view of a plurality of adjacent pixel groups of a TFT array substrate on which data lines, scanning lines, pixel electrodes, and the like are formed. FIG. 3 is a sectional view taken along plane A-A' of FIG. 2. In FIG. 3, respective layers and components have a different reduction ratio so that they are shown in a size which can be recognized on the figure.

[0089] In FIG. 1, a pixel electrode 9a and a TFT 30 that controls the switching of the pixel electrode 9a are formed at each of a plurality of pixels formed in a matrix shape to constitute the image display region of the electro-optical device in this embodiment. A data line 6a to which an image signal is supplied is electrically connected to the source of the TFT 30. Image signals S1, S2, . . . Sn to be written to the data lines 6a may be supplied in this order in the sequence of the data lines 6a or may be supplied to the plurality of adjacent data lines 6a in each group. Further, scanning lines 3a are electrically connected to the gates of TFTs 30 and pulsewise scanning signals G1, G2, . . . Gm are sequentially applied to the scanning lines 3a in this order in the sequence of the scanning line 3a. The pixel electrodes 9a are electrically connected to the drains of the TFTs 30, and the image signals S1, S2, . . . Sn supplied from the data lines 6a are written to the pixel electrodes 9a at predetermined timing by turning off the TFTs 30 acting as switching elements for a predetermined period of time. The image signals S1, S2, . . . Sn of a predetermined level, written to liquid crystal as an example of an electro-optical substance through the pixel electrode 9a, are maintained between the pixel electrodes 9a and the confronting electrodes (to be described later) formed on a confronting substrate (to be described later) for a predetermined period. The liquid crystal modulates light beams and permits a gradation display by changing the orientation and order of aggregated modules based on the level of a voltage applied thereto. When a normally-white mode is employed, the transmittance of incident light beams is reduced in accordance with a voltage applied in a unit of the respective pixels, whereas, when a normally-black mode is employed, the transmittance of incident light beams is increased in accordance with a voltage applied in a unit of the respective pixels, so that light beams having a contrast in accordance with an image signal are emerged from the electro-optical device as a whole. Storage capacitors 70 are added in parallel with liquid crystal capacitors formed between the pixel electrodes 9a and the confronting electrodes to prevent leakage of the thus maintained image signal.

[0090] In FIG. 2, the plurality of transparent pixel electrodes 9a (the outline of each of which is shown by a dotted line portion 9a') are formed on the TFT array substrate of the electro-optical device, and the data lines 6a and the scanning lines 3a are disposed along the longitudinal and lateral interfaces of the pixel electrodes 9a.

[0091] Further, the scanning lines 3a are disposed so as to face the channel regions 1a', which are shown by oblique lines inclining upward in the right direction in the figure, of a semiconductor layer 1a, and the scanning lines 3a act as gate electrodes (in particular, in this embodiment, the scanning lines 3a are widened at portions where they act as the gate electrodes). As described above, the pixel switching TFTs 30, each of which has a scanning line 3a as a gate electrode in each channel region a' in confrontation there-

with, are disposed at the positions where the scanning lines **3a** intersect the data lines **6a**.

[0092] As shown in **FIGS. 2 and 3**, in this embodiment, each capacitance line **300** has a multi-layer structure in which a first film **72**, formed of a conductive polysilicon film, or the like, and a second film **73** formed of a metal silicide film or the like containing a high melting point metal, are laminated. Of these films, the second film **73** has a function as a shading layer to shade a TFT **30** from incident light beams on the upper side of the TFT **30**, in addition to a function as the capacitance line **300** or a capacitance electrode of the storage capacitor **70** on the fixed potential side thereof. Further, the first film **72** has a function as a light absorbing layer interposed between the second film **73** as the shading layer and the TFT **30**, in addition to the function as the capacitance line **300** or the fixed potential side capacitance electrode of the storage capacitor **70**. In contrast, each transit layer **71a** disposed facing each capacitance line **300** through a dielectric film **75** has a function as a light absorbing layer interposed between the second film **73** acting as the shading layer and the TFT **30**, in addition to a function as the pixel potential side capacitance electrode of the storage capacitor **70**, and further has a function as an intermediate conductor layer to transit and connecting the pixel electrodes **9a** and the heavily doped drain regions **1e** of the TFTs **30**. This shading and light absorption will be described below in detail with reference to **FIGS. 4 to 7**. The first film **72** and the transit layer **71a** acting as the light absorption layers are formed of a material such as a polysilicon film having a higher light absorption factor as compared with the second film **73** acting as the shading layer.

[0093] In this embodiment, the storage capacitor **70** is formed of the transit layer **71a**, which acts as the pixel potential side capacitance electrode connected to the heavily doped drain region **1e** of the TFT **30** (and the pixel electrode **9a**), and a part of the capacitance line **300**, which acts as the fixed potential side capacitance electrode, wherein the transit layer **71a** and the part of the capacitance line **300** are disposed in confrontation with each other through the dielectric film **75**.

[0094] Each capacitance line **300** extends along each scanning line **3a** in a striped shape, and the portion thereof overlapping a TFT **30** projects upward and downward in **FIG. 2**. Then, a shading layer, which has a lattice shape when observed in plan view, are formed above the TFTs **30** on the TFT array substrate **10** in such an arrangement that the data lines **6a** extending in a longitudinal direction in **FIG. 2** intersect with the capacitance lines **300** extending in a lateral direction in **FIG. 2**. The shading layer prescribes the opening regions of the respective pixels.

[0095] In contrast, a lower shading film **11a** is formed in a lattice shape under the TFTs **30** on the TFT array substrate **10**.

[0096] In this embodiment, the region where the lattice-shaped lower shading film **11a** is formed is located within the region where the upper shading layer (that is, the capacitance lines **300** and the data lines **6a**) having the lattice shape likewise is formed (that is, the former region is formed slightly smaller than the latter region and the lower shading film **11a** is formed narrower than the widths of the capacitance line **300** and the data lines **6a**). Then, the channel

regions **1a'** of the TFTs **30**, which include the portions where the lightly doped source regions **1b** of the TFTs **30** are connected to the lightly doped drain regions **1c** (that is, LDD regions) thereof, are located within the intersecting regions of the lattice-shaped lower shading film **11a**.

[0097] The second film **73** and the lower shading film **11a**, constituting an example of the shading layer, are formed of single metal, alloy, metal silicide, poly-silicide, a laminated film thereof, or the like containing at least one of high melting point metals, for example, Ti, Cr, W, Ta, Mo, Pb, and the like, respectively. Further, each capacitance line **300** containing the second film **73** has the multi-layer structure, and the first film **72** thereof is formed of the conductive polysilicon film. While it is not necessary to form the second film **73** of a conductive material, if not only the first film **72** but also the second film **73** are formed of a conductive film, the resistance of the capacitance line **300** can be more reduced.

[0098] Further, in **FIG. 3**, each of the dielectric films **75** interposed between a transit layer **71a** and a capacitance line **300**, acting as the capacitance electrode, is composed of a silicon oxide film such as a relatively thin HTO film, LTO film or the like having a film thickness of, for example, 5 to 200 nm, a silicon nitride film, or the like. From a viewpoint of increasing the capacitance of each storage capacitor **70**, it is preferable that the dielectric film **75** be as thin as possible as long as the reliability thereof can be sufficiently obtained.

[0099] Each of the first films **72**, which acts as not only the light absorption layer but also constitutes a portion of each capacitance line **300**, is formed of, for example, a polysilicon film having a film thickness of about 150 nm. Further, the second film **73**, which acts not only as the light absorption layer but also constitutes another portion of each capacitance line **300**, is formed of a tungsten silicide film having a film thickness of, for example, about 150 nm. Since the first film **72**, disposed on the side which is in contact with the dielectric film **75**, is formed of the polysilicon film and the transit layer **71a**, which is in contact with the dielectric film **75**, is formed of the polysilicon film, the deterioration of the dielectric film **75** can be prevented. For example, if an arrangement in which a metal silicide film comes into contact with the dielectric film **75**, metal, such as heavy metal and the like, enters the dielectric film **75**, whereby the performance of the dielectric film **75** is deteriorated. Further, in the formation of the capacitance lines **300** on the dielectric films **75**, when the capacitance lines **300** are formed continuously without executing a photoresist process after the dielectric films **75** are formed, the quality of the dielectric films **75** can be increased, whereby the dielectric films **75** can be formed thin and finally the capacitances of the storage capacitors **70** can be increased.

[0100] As shown in **FIGS. 2 and 3**, each data line **6a** is connected to a transiting and connecting transit layer **71b** through a contact hole **81**, and further the transit layer **71b** is electrically connected to the heavily doped source region **1d**, which is formed of, for example, a polysilicon film, of the semiconductor layer **1a**. The transit layer **71b** is formed of the same film as that of the transit layer **71a** having the above-mentioned functions.

[0101] Further, each capacitance line **300** extends from the image display region in which the pixel electrode **9a** is disposed to the periphery thereof, is electrically connected to

a constant potential source, and set to a fixed potential. This will be described below in detail with reference to **FIGS. 8 and 9**.

[0102] Each pixel electrode **9a** is electrically connected to the heavily doped drain region **1e** of each semiconductor layer **1a** through the transit layer **71a** as well as the contact holes **83** and **85**. More specifically, in this embodiment, the transit layer **71a** achieves a function for transiting and connecting the pixel electrodes **9a** to the TFTs **30**, in addition to the function as the pixel potential side capacitance electrode of the storage capacitor **70** and the function as the light absorption layer. When the transit layers **71a** and **71b** are used as the transit layers, even if the interlayer distance therebetween is set to a long distance of, for example, about 2000 nm, the transit layers **71a** and **71b** can be excellently connected to each other through at least two series contact holes each having a relatively small diameter while avoiding a technical difficulty of connecting them through one contact hole, which can increase the opening ratio of the pixels and is useful to prevent etching from passing through contact holes when they are opened.

[0103] In **FIGS. 2 and 3**, the electro-optical device includes the transparent TFT array substrate **10** and the transparent confronting substrate **20** disposed in confrontation with the TFT array substrate **10**. The TFT array substrate **10** is formed of, for example, a quartz substrate, a glass substrate, or a silicon substrate, and the confronting substrate **20** is formed of, for example, a glass substrate or a quartz substrate.

[0104] The TFT array substrate **10** has grooves **10CV** formed thereon which have a lattice shape when observed on a plan view (shown by a region of oblique lines inclining downward in the right direction). The wiring and the elements, such as the scanning lines **3a**, the data lines **6a**, the TFTs **30**, and the like, are buried in the grooves **10CV**. This arrangement eases the steps between the regions where the wiring, the elements and the like exist and the regions where they do not exist, so that defective images, such as faulty orientation of liquid crystal, and the like, caused by the steps can finally be reduced.

[0105] As shown in **FIG. 3**, the pixel electrode **9a** is disposed on the TFT array substrate **10**, and an orientation film **16**, having been subjected to predetermined orientation processing, such as rubbing processing or the like, is disposed above the pixel electrode **9a**. The pixel electrode **9a** is formed of a transparent conductive thin film such as an ITO (indium tin oxide) film or the like. Further, the orientation film **16** is formed of, for example, an organic film such as a polyimide film or the like.

[0106] In contrast, a confronting electrode **21** is disposed on the entire surface of the confronting substrate **20**, and an orientation film **22** having been subjected to predetermined orientation processing such as rubbing processing or the like is disposed under the confronting electrode **21**. The confronting electrode **21** is formed of a transparent conductive film, such as an ITO film or the like. Further, the orientation film **22** is formed of an organic film, such as a polyimide film or the like.

[0107] A shading film of a lattice shape or a stripe shape may be disposed on the confronting substrate **20**. The shading film on the confronting substrate **20** can more

reliably prevent incident light beams from entering the channel regions **1a'**, the lightly doped source regions **1b** and the lightly doped drain regions **1c** from the confronting substrate **20** side in cooperation with the capacitance lines **300** and the data lines **6a** which constitute the shading film as described above. Further, when at least the surface, to which incident light beams are irradiated, of the shading film on the confronting substrate **20** is formed of a highly reflective film, the shading film acts to prevent an increase in the temperature of the electro-optical device. It is preferable that the shading film on the confronting substrate **20** be formed inwardly of the shading layer formed of the capacitance lines **300** and the data lines **6a** when observed in plan view. With this arrangement, an effect of shading light beams and preventing a temperature increase can be obtained by the shading film on the confronting substrate **20** without reducing the opening ratio of the respective pixels.

[0108] A liquid crystal layer **50** is formed by inserting liquid crystal as an example of an electro-optical substance in the space surrounded by a seal member, to be described below, between the TFT array substrate **10** and the confronting substrate **20**, which are arranged as described above and disposed so that the pixel electrode **9** faces the confronting electrode **21**. The liquid crystal layer **50** is placed into a predetermined orientation state by the orientation films **16** and **20** in a state in which no electric field is applied thereto from the pixel electrodes **9a**. The liquid crystal layer **50** is formed of liquid crystal with which nematic liquid crystals of, for example, one or a plurality of kinds are mixed. The seal member is an adhesive formed of, for example, a photo-curing or thermosetting resin for bonding the TFT array substrate **10** to the confronting substrate **20** around the peripheries thereof, and a gap agent, such as glass fiber, glass beads, or the like, is mixed therewith to set the distance between both the substrates to a predetermined value.

[0109] Further, an underlayer insulation film **12** is disposed under the pixel switching TFT **30**. The underlayer insulation film **12**, which is formed on the entire surface of the TFT array substrate **10**, has a function for preventing the characteristics of the pixel switching TFT **30** from being deteriorated by the surface of the TFT array substrate **10** which is made rough in polishing and by the stain and the like remaining after the TFT array substrate **10** is washed, in addition to a function for interlayer-insulating the TFT **30** from the lower shading film **11a**.

[0110] In **FIG. 3**, the pixel switching TFT **30** has a LDD (lightly doped drain) structure and includes the scanning line **3a**, the channel region **1a'** of the semiconductor layer **1a** to which a channel is formed by an electric field from the scanning line **3a**, an insulation thin film **2** including a gate insulation film for insulating the scanning line **3a** and the semiconductor layer **1a**, the lightly doped source and drain regions **1b** and **1c** of the semiconductor layer **1a**, and the heavily doped source and drain regions **1d** and **1e** thereof.

[0111] A first interlayer insulation film **41**, to which the contact hole **82** connecting to the heavily doped source region **1d** and the contact hole **83** connecting to the heavily doped drain region **1e** are formed, respectively, is formed on the scanning line **3a**.

[0112] The transit layers **71a** and **71b** and the capacitance line **300** are formed on and above the first interlayer insulation film **41**, and a second interlayer insulation film **42**, to

which the contact holes **82** and **85** connecting to the transit layers **71a** and **71b**, respectively, is formed thereon and thereabove.

[0113] In this embodiment, the ions implemented into the polysilicon films constituting the semiconductor layer **1a** and the scanning line **3a** may be activated by baking the first interlayer insulation film **41** at 1000° C. In contrast, the stress generated in the vicinity of the interface of the capacitance line **300** may be eased by not subjecting the second interlayer insulation film **42** to the baking.

[0114] The data lines **6a** is formed on the second interlayer insulation film **42**, and a third interlayer insulation film **43**, to which the contact hole **85** connecting to the transit layer **71a** is formed, is formed thereon. The pixel electrode **9a** is formed on the upper surface of the third interlayer insulation film **43** arranged as described above.

[0115] The light absorption layers **72** and **71a** are formed of a material the light absorption property of which is higher than that of the underlayer insulation film **12** and the respective interlayer insulation films **41**, **42**, and **43**.

[0116] According to this embodiment arranged as described above, when light beams tend to be incident on the channel region **1a'** of the TFT **30** and its vicinity from the confronting substrate **20** side, the light beams are shaded with the lattice-shaped shading layer formed of the data line **6a** and the capacitance line **300** (in particular, the second film **73** thereof). In contrast, when return light beams tend to be incident on the channel region **1a'** of the TFT **30** and its vicinity from the TFT array substrate **10** side, the light beams are shaded with the lower shading film **11a** (which is effective in particular when one optical system is arranged by a combination of a plurality of electro-optical devices through a prism and the like in a double-panel type color display projector and the like, because return light beams formed of a projected light component passing through the prism and the like from other electro-optical device is strong). Then, internally-reflected light beams, multipath-reflected light beams and the like, which are generated by oblique return light beams incident on the data line **6a** formed of the A1 film having the high reflectance and on the inner surface of the second film **73** (that is, the surface thereof facing the TFT **30**), are absorbed and removed by the first film **72** and the transit layer **71a** acting as the light absorption layers. As a result, the characteristics of the TFT **30** are hardly deteriorated by light leakage, and a very high light resistant property can be obtained in the electro-optical device.

[0117] In particular, in this embodiment, since the first film **72** and the transit layer **71a** acting as the light absorption layers are formed of the polysilicon film made conductive (or a silicon film such as amorphous silicon or the like) and the channel region also is formed of the polysilicon film to which any of P, B, As and the like is doped to control a threshold voltage V_{th} or to which none of them is not doped (or a silicon film such as amorphous silicon or the like), the light absorption layers have a light absorbing property similar to, or the same as, the light absorbing property (frequency dependent property and the like) in the channel region. Therefore, this arrangement is advantageous in that light beams including a frequency component, which acts as a cause of light leakage when it is absorbed by the channel region **1a'**, are absorbed and removed by the first film **72** and

the transit layer **71a**. That is, the effect of a light absorbing property is increased by forming the TFT channel and the light absorption layers of the same main material.

[0118] Next, shading and light absorption executed in this embodiment will be further described with reference to FIGS. **4** to **7**. FIG. **4** is a pictorial plan view showing the upper and lower shading films in the image display region by extracting and enlarging them, and FIGS. **5** and **6** are pictorial sectional views showing how light beams are shaded and absorbed in the B-B' section of FIG. **4**. Further, FIG. **7** is a pictorial sectional view showing how light beams are shaded and absorbed in the same B-B' section of FIG. **4** in a modified embodiment.

[0119] As shown in FIG. **4**, in this embodiment, the non-opening region of the respective pixels is prescribed in a lattice shape by the shading layer formed of the capacitance lines **300** and the data lines **6a** (at the positions where the capacitance lines **300** are discontinued to form the contact holes **81** and **82**). Accordingly, these capacitance lines **300** and data lines **6a** can effectively prevent a contrast ratio from being lowered by the occurrence of light leakage. These capacitance lines **300** and data lines **6a** are disposed above the TFTs **30** in a lattice shape and the lower shading film **11a** disposed in a lattice shape is located below the TFTs **30**, and the region where the lower shading film **11a** is formed is located within the region where the lattice-shaped shading layer composed of the capacitance line **300** and the data line **6a** is formed.

[0120] Thus, as shown in FIG. **5**, the second film **73** of the capacitance line **300** and the data line **6a** act as a shading layer with respect to incident light beams **L1** which are incident from the upper side in the electro-optical device (that is, from the incident side of the incident light beams). Accordingly, the incident light beams **L1** can be prevented from reaching the TFT **30**. Further, the lower shading film **1a** is formed slightly smaller than the upper shading layer (that is, the second film **73** of the capacitance line **300** and the data line **6a**), which reduces the occurrence of internally-reflected light beams and multipath-reflected light beams which result from that the oblique component contained in the incident light beams **L1** passes aside the upper shading layer (capacitance line **300** and data line **6a**) and is reflected by the inner surface of the lower shading film **11a**.

[0121] In contrast, as shown in FIG. **6**, the lower shading film **11a** acts as a shading layer with respect to return light beams **L2** which are incident from the lower side in the electro-optical device (that is, from the side from which incident light beams emerge). Accordingly, the return light beams **L2** can be prevented from reaching the TFTs **30**. Further, since the lower shading film **11a** is formed slightly smaller than the upper shading layer (that is, the second film **73** of the capacitance line **300** and the data line **6a**), the oblique component contained in the return light beams **L2** partly passes aside the lower shading film **11a** and advances toward the inner surface of the upper shading layer (in particular, toward the inner surface of the capacitance line **300**). However, since the light absorption layers (that is, the first film **72** of the capacitance line **300** and the transit layer **71a**) are interposed between the upper shading layer (that is, the second films **73** of the capacitance line **300** and the data line **6a**) and the TFT **30**, the oblique component contained in the return light beams **L2** as well as inner-surface-

reflected light beams L3 and multipath-reflected light beams L4 which are caused by that the above component is reflected by the inner surface of the upper shading layer (that is, the second film 73 of the capacitance line 300 and the data line 6a) are absorbed and removed by the light absorption layers.

[0122] From a result of the above-mentioned structure, deterioration of the pixel switching TFTs 30 caused by light leakage can be reduced by increasing a light resistant property while increasing the opening ratio of the respective pixels by the embodiment, which finally permits a bright image of high quality having a high contrast ratio to be displayed.

[0123] In the embodiment, it is preferable that the second film 73 constituting the shading layer have a heat conductivity which is higher than that of the first film 72 and the transit layer 71a constituting the light absorption layers. Accordingly, the heat generated in the first film 72 and the transit layer 71a when they absorb light beams can escape through the second film 73 having the higher heat conductivity. That is, the quantity of heat transmitted to the TFTs 30 from the first film 72 and the transit layer 71a can be reduced, whereby the heat leakage caused by the TFTs 30 can be reduced. As a result of the above mentioned, the transistor characteristics of the TFTs 30 can be greatly enhanced by reducing both the light leakage and the heat leakage.

[0124] Further, from the view point of reducing the heat leakage of the TFT 30, it is preferable that the first interlayer insulation film 41 interposed between the transit layer 71a acting as the light absorption layer and the TFT 30 be set larger than the dielectric film 75 interposed between the transit layer 71a and the capacitance line 300 having the function for escaping heat as described above. When the first interlayer insulation film 41 is set as described above, the heat generated by the transit layer 71a when it absorbs light beams can more effectively escape through the capacitance line 300.

[0125] In the embodiment shown in FIGS. 4 to 6, since the lower shading film 11a is formed slightly smaller than the upper shading layer (that is, the second film 73 of the capacitance line 300 and the data line 6a) it is difficult for the oblique component contained in the incident light beams L1 to reach the inner surface of the lower shading film 11a. However, the inner-surface-reflected light beams and the multipath-reflected light beams, which are caused by the obliquely incident light beams L1 reflected by the inner surface of the lower shading film 11a, become a problem depending upon the specification of the device (for example, depending on a degree of reduction of the size of the lower shading film 11a and on a degree of oblique angle applied to the incident light beams).

[0126] In this case, it is sufficient to dispose a light absorption layer 11b also on the inner surface of the lower shading film 11a, as shown in a modified embodiment shown in FIG. 7. With this arrangement, it is possible for the light absorption layer 11b to absorb and remove the obliquely incident light beams L1 reaching the inner surface of the lower shading film 11a as well as the inner-surface-reflected light beams L3 and the multipath-reflected light beams L4 resulting from the obliquely incident light beams

L1. It is preferable that a main material which forms the light absorption layer 11b is the same as that for forming the channel region.

[0127] Further, as another modified embodiment, a modified embodiment shown in FIG. 8 may be employed. The lower shading film 11a is formed inwardly of the upper shading films 73 and 6a, and the lower light absorption layer 11b is formed wider than the lower shading film 11a. With this arrangement, the obliquely incident light beams L1 can be absorbed and removed by the lower absorption layer 11b or the upper absorption layers 71a and 72. Further, since the obliquely incident light beams L1 having passed through the lower absorption layer 11b can pass therethrough without being reflected by the lower shading film 11a, they do not reach the semiconductor layers of the TFT 30.

[0128] In the modified embodiment of FIG. 8, while the lower absorption layer 11b is shown as being approximately as wide as the upper absorption layers 71a and 72, it may be formed inwardly of the upper absorption layers 71a and 72 or may be formed wider than them.

[0129] Next, an arrangement in which the capacitance lines 300 are used as a fixed potential will be described with reference to FIGS. 9 and 10. FIG. 9 is a plan view showing an example of an arrangement in which capacitance lines 300 are connected to a constant potential source, and FIG. 10 is a plan view showing another example of the arrangement in which the capacitance lines 300 are connected to the constant potential source.

[0130] As shown in FIGS. 9 and 10, the capacitance lines 300, which are formed approximately in a stripe shape in an image display region 10a, preferably extend to a peripheral region located in the periphery of the image display region 10a so that they are arranged as a single unit. Then, the capacitance lines 300 may be connected to, for example, constant potential wiring 303 as a whole through the contact holes 302 disposed at the four corners of the TFT array substrate 10, as shown in FIG. 9. Otherwise, they may be connected to constant potential wiring 303' through a plurality of contact holes 302' disposed redundantly as shown in FIG. 10. Note that in FIGS. 9 and 10, the constant potential wiring 303 and 303' is preferably formed of an A1 film having a low resistance similarly to the data lines 6a.

[0131] Further, a constant potential source, to which the constant potential wiring 303 and 303' is connected, may be a constant potential source acting as a positive power supply or a negative power supply which is supplied to a scanning line drive circuit (to be described below) to supply a scanning signal for driving the TFTs 30 to the scanning lines 3a or to a data line drive circuit (to be described later) to control a sampling circuit that supplies an image signal to the data lines 6a. Otherwise, the constant potential source may be a constant potential source supplied to the confronting electrodes 21 of the confronting substrate 20.

[0132] It is preferable to extend the lower shading film 11a disposed below the TFTs 30 from the image display region to its periphery similarly to the capacitance lines 300 and to connect the lower shading film 11a to the constant potential source to avoid that the variation of potential thereof adversely affects the TFTs 30.

[0133] In the embodiment described above, the occurrence of steps, which would be formed in the regions along the

data lines **6a** and the scanning lines **3a** on the underlayer surface of the pixel electrodes **9a** (that is, on the surface of the third interlayer insulation film **43**) by laminating the plurality of conductive layers as shown in **FIG. 3**, is eased by forming the grooves **10CV** on the TFT array substrate **10**. In place of or in addition to the grooves **10CV**, however, flattening processing may be executed by forming grooves on the underlayer insulation film **12**, the first interlayer insulation film **41**, the second interlayer insulation film **42**, and the third interlayer insulation film **43** and by burying the wiring such as the data lines **6a** and the like, the TFTs **30** and so on. Otherwise, the flattening processing may be executed by polishing the steps on the upper surfaces of the third and second interlayer insulation films **43** and **42** by means of CMP (chemical mechanical polishing) or the like or by flattening them using organic SOG.

[0134] Further, in the above-mentioned embodiment, while the pixel switching TFT **30** preferably has the LDD structure as shown in **FIG. 3**, it may have an offset structure in which no impurity is implanted into the low concentration source and drain regions **1b** and **1c** or may be arranged as a self-alignment type TFT in which impurities are implanted in a high concentration using the gate electrodes formed of a part of the scanning lines **3a** as masks so as to form a high concentration source and drain regions in a self-alignment fashion. Further, while this embodiment is arranged as a single gate structure in which only one gate electrode of the pixel switching TFT **30** is interposed between the high concentration source and drain regions **1d** and **1e**, at least two gate electrodes may be interposed therebetween. When the TFT is arranged with the dual gates or at least with the triple gates, the leakage current at the joints of the channel, source and drain regions can be reduced or prevented, whereby a current can be reduced when the TFT is turned off. (Overall arrangement of electro-optical device)

[0135] An overall arrangement of the electro-optical device in the respective embodiments constructed as described above will be described with reference to **FIGS. 11** to **12**. Note that **FIG. 11** is a plan view in which the TFT array substrate **10** is viewed from the confronting substrate **20** side together with the respective constitutional elements formed thereon, and **FIG. 12** is a sectional view taken along plane H-H' of **FIG. 11**.

[0136] In **FIG. 12**, a seal member **52** is disposed on the TFT array substrate **10** along the edge thereof and a shading film **53**, which acts as a frame for prescribing the periphery of the image display region **10a**, is disposed inwardly of the seal member **52** in parallel therewith. A data line drive circuit **101** for driving the data lines **6a** by supplying an image signal thereto at predetermined timing and an external circuit connecting terminals **102** are disposed along one side of the TFT array substrate **10** in a region outside of the seal member **52**, and scanning line drive circuits **104** are disposed along two sides of the TFT array substrate **10** adjacent to the one side thereof to drive the scanning lines **3a** by supplying a scanning signal thereto at predetermined timing. A scanning line drive circuit **104** may be disposed on only one side of the TFT array substrate **10** if no problem is caused by delay of a scanning signal to be supplied to the scanning lines **3a**. Further, data line drive circuits **101** may be disposed along both sides of the image display region **10a**. Further, a plurality of pieces of wiring **105** are disposed along the remaining one side of the TFT array substrate **10**

to connect the scanning line drive circuits **104** disposed on both the sides of the image display region **10a**. Further, a conductor **106** is disposed to at least one of the corners of the confronting substrate **20** to make electric conduction between the TFT array substrate **10** and the confronting substrate **20**. Then, as shown in **FIG. 12**, the confronting substrate **20**, which has substantially the same outline as that of the seal member **52** shown in **FIG. 11**, is secured to the TFT array substrate **10** by the seal member **52**.

[0137] A sampling circuit that applies an image signal to the plurality of data lines **6a** at predetermined timing, a precharge circuit that supplies a precharge signal of a predetermined voltage level to the plurality of data lines **6a** prior to the image signal, an inspection circuit that inspects the quality, defect and the like of the electro-optical device while it is being manufactured or when it is shipped, and the like may be formed on the TFT array substrate **10**, in addition to the data line drive circuit **101**, the scanning line drive circuits **104** and the like.

[0138] In the embodiments described with reference to **FIGS. 1** to **12**, the data line drive circuit **101** and the scanning line drive circuits **104** may be electrically and mechanically connected to a driving LSI mounted on, for example, a TAB (tape automated bonding) substrate through an anisotropic conductive film disposed to the periphery of the TFT array substrate **10** in place of that they are disposed on the TFT array substrate **10**. Further, a polarizing film, a phase difference film, a polarizer, and the like are disposed on the side of the confronting substrate **20** on which projected light beams are incident and on the side of the TFT array substrate **10** from which light beams emerge depending upon operation modes, for example, a TN mode, a VA (vertically aligned) mode, a PDLC (polymer dispersed liquid crystal) mode, and the like and depending on a normally white and a normally black mode.

[0139] The electro-optical device of the embodiments described above is applied to a projector as, for example, a light bulb.

[0140] **FIG. 13** is a plan view showing an arrangement of the projector. As shown in **FIG. 13**, a lamp unit **2102**, which is formed of a white light source, such as a halogen lamp, is disposed in the projector **2100**. Projected light beams emitted from the lamp unit **2102** are separated into three primary colors of RGB by three mirrors **2106** and two dichroic mirrors **2108** disposed in the projector **2100** and introduced to light bulbs **100R**, **100G**, and **100B** corresponding to the respective primary colors, respectively. The light bulbs **100R**, **100G**, and **100B** are arranged similarly to a liquid crystal panel **100** according to the above-mentioned embodiments and driven in response to primary color signals of R, G, B supplied from a processing circuit (not shown) to which an image signal is inputted, respectively. Further, since light beams of B color have a longer light path as compared with other light beams of R color and G color, they are introduced through a relay lens system **2121** composed of an incident light lens **2122**, a relay lens **2123**, and a light emitting lens **2124**.

[0141] Incidentally, the light beams, which have been modulated by the light bulbs **100R**, **100G** and **100B**, respectively, are incident on a dichroic prism **2112** from three directions. Then, the light beams of R and B colors are refracted at 90° by the dichroic prism **2112**, whereas the light

beams of G color advance straight. Therefore, after the images the respective colors are combined, a color image is projected on a screen **2120** by a projecting lens **2114**.

[0142] Note that since light beams corresponding to the respective primary colors of R, G, and B are incident on the light bulbs **100R**, **100G**, and **100B** through the dichroic mirrors **2108**, a color filter need not be provided therewith. Further, the images having passed through the light bulbs **100R** and **100B** are projected after they are reflected by the dichroic prism **2112**, whereas the image having passed through the light bulb **100G** is projected as it is. Thus, the images displayed by the light bulbs **100R** and **100B** are reversed laterally with respect to the image displayed by the light bulb **100G**.

[0143] In the above-mentioned embodiments, no color filter is provided with the confronting substrate **20**. However, RGB color filters may be formed on the confronting substrate **20** in predetermined regions confronting the pixel electrodes **9a** together with the protective films thereof. With this arrangement, the electro-optical device of the respective embodiments can be applied to a direct-observing type or reflecting type color electro-optical device, in addition to the projector.

[0144] Further, microlenses may be formed on the confronting substrate **20** so that one microlens corresponds to one pixel. Otherwise, color filter layers formed of a color resist or the like may be formed under the pixel electrodes **9a** corresponding to RGB on the TFT array substrate **10**. With this arrangement, a bright electro-optical device can be realized by enhancing an incident light converging efficiency. Further, a dichroic filter for creating RGB colors making use of light interference may be formed by depositing several interference layers having a different refractive index on the confronting substrate **20**. According to the confronting substrate provided with the dichroic filter, a brighter electro-optical device can be realized.

[0145] The electro-optical device of the present invention can be applied to the display device of a mobile type personal computer and the display device of a mobile phone as well as to a liquid crystal television, view-finder type and monitor-direct-observing type video tape recorders, car navigation device, pager, electronic notebook, electronic calculator, word processor, workstation, TV phone, POS terminal, digital still camera, electronic equipment provided with a touch panel, and the like as other application examples.

[0146] The present invention is by no means limited to the above-mentioned embodiments and can be suitably modified within a range which is not contrary to the gist and spirit of the present invention which are read from the following claims and the overall specification, and it is needless to say that electro-optical devices and methods of manufacturing them that are modified as described above also are included in the technical scope of the present invention.

What is claimed is:

1. An electro-optical device, comprising:
 - a pair of substrates;
 - an electro-optical substance interposed between said pair of substrates;
 - pixel electrodes formed on one of said pair of substrates;

thin film transistors connected to said pixel electrodes, the thin film transistors having channel regions;

a shading layer that covers at least the channel regions of said thin film transistors; and

a light absorption layer interposed between said shading layer and said thin film transistors.

2. The electro-optical device according to claim 1, said light absorption layer substantially including a material which mainly forms the channel regions of said thin film transistors.

3. The electro-optical device according to claim 1, said light absorption layer including a silicon film.

4. The electro-optical device according to claim 1, said shading layer including a film containing metal.

5. The electro-optical device according to claim 1, said shading layer being disposed above said thin film transistors on said substrate.

6. The electro-optical device according to claim 5, said shading layer including data lines.

7. The electro-optical device according to claim 5,

the shading layer including capacitance lines interposed between said data lines and said thin film transistors; and

the light absorption layer including capacitance electrodes disposed in confrontation with said capacitance lines through a dielectric film and separated in an island shape for each pixel.

8. The electro-optical device according to claim 5, said shading film including:

a plurality of data lines connected to said thin film transistors and extending in a first direction, respectively; and

a plurality of capacitance lines connected to said pixel electrodes and extending in a second direction intersecting the first direction, respectively.

9. The electro-optical device according to claim 5,

said shading layer including one layer of capacitance lines interposed between data lines and said thin film transistors and having a multilayer structure; and

said light absorption layer including another layer of said capacitance lines that is located nearer to said thin film transistors than said one layer.

10. The electro-optical device according to claim 7, said capacitance lines being formed in a stripe shape extending in a direction intersecting said data lines in an image display region as well as connected to a constant potential source located in a peripheral region located in the vicinity of said image display region.

11. The electro-optical device according to claim 10, said capacitance lines being connected to each other in the peripheral region and connected to said constant potential source as a whole through one or a plurality of contacts.

12. The electro-optical device according to claim 10, said capacitance lines being connected to each other in the peripheral region and redundantly connected to said constant potential source through a plurality of contacts.

13. The electro-optical device according to claim 5, further comprising another shading layer disposed below said thin film transistors on said substrate that covers at least the channel regions of said thin film transistors.

14. The electro-optical device according to claim 13, further comprising another light absorption layer interposed between said other shading layer and said thin film transistors, and substantially including a material which mainly forms the channel regions of said thin film transistors.

15. The electro-optical device according to claim 1, said shading layer being disposed below said thin film transistors on said substrate.

16. The electro-optical device according to claim 1, said light absorption layer including a portion that includes an intermediate conductor layer that transits and connects said pixel electrodes or said data lines to said thin film transistors.

17. The electro-optical device according to claim 1, said shading layer having a heat conductivity higher than that of said light absorption layer.

18. The electro-optical device according to claim 17, the interlayer distance between said thin film transistors and said light absorption layer being larger than that between said light absorption layer and said shading layer.

19. The electro-optical device according to claim 1, said shading layer being laminated on said light absorption layer through an insulation film as well as formed slightly larger than said light absorption layer when observed on a plan view.

20. An electro-optical device, comprising:

a pair of substrates;

an electro-optical substance interposed between said pair of substrates;

pixel electrodes formed on one of said pair of substrates;

thin film transistors connected to said pixel electrodes, the thin film transistors having channel regions;

a first shading layer that covers at least the channel regions of said thin film transistors; and

a first light absorption layer facing said first shading layer through said thin film transistors.

21. The electro-optical device according to claim 20, said first shading layer being disposed on a light incident side with respect to said thin film transistors.

22. The electro-optical device according to claim 20, a second light absorption layer being further interposed between said first shading layer and said thin film transistors.

23. The electro-optical device according to claim 20, a second shading layer being further disposed on a side opposite to said first light absorption layer with respect to said thin film transistors.

24. The electro-optical device according to claim 23, said second shading layer being formed in a region inside of said first light absorption layer.

25. The electro-optical device according to claim 24, said second shading layer being formed in a region inside of said first shading layer.

26. An electro-optical device, comprising:

a pair of substrates;

an electro-optical substance interposed between said pair of substrates;

pixel electrodes formed on one of said pair of substrates;

thin film transistors connected to said pixel electrodes, the thin film transistors having channel regions;

a first light absorption layer that covers at least the channel regions of said thin film transistors; and

a second light absorption layer facing said first light absorption layer through said thin film transistors.

27. The electro-optical device according to claim 26, further including light transmitting insulation films interposed among said pixel electrodes, said thin film transistors, and said first light absorption layer, respectively.

28. A projecting type display device, comprising:

a light source;

light bulbs, each light bulb including an electro-optical device according to claim 1;

light conductors that introduce light beams emitted from said light source to said light bulbs; and

a projecting optical member that projects light beams modulated by said light bulbs.

29. A substrate for electro-optical device, comprising:

pixel electrodes;

thin film transistors connected to said pixel electrodes;

a shading layer that covers at least the channel regions of said thin film transistors; and

a light absorption layer interposed between said shading layer and said thin film transistors.

30. A substrate for electro-optical device, comprising:

pixel electrodes;

thin film transistors connected to said pixel electrodes, the thin film transistors having channel regions;

a shading layer that covers at least the channel regions of said thin film transistors; and

a light absorption layer facing said shading layer through said thin film transistors.

31. A substrate for electro-optical device, comprising:

pixel electrodes;

thin film transistors connected to said pixel electrodes, the thin film transistors having channel regions;

a first light absorption layer that covers at least the channel regions of said thin film transistors; and

a second light absorption layer facing said first light absorption layer through said thin film transistors.

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